

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

SS32-MS THRU SS3200-MS

Product specification


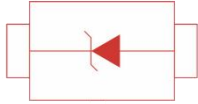
Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250 °C/10 seconds at terminals


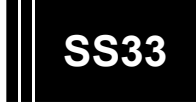






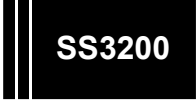
MECHANICAL DATA

- Case : JEDEC DO-214AC/SMA molded plastic body
- Terminals : Solderable per MIL-STD-750, Method 2026
- Polarity : Color band denotes cathode end Mounting
- Position: Any
- Weight : 0.0018 ounce, 0.064 grams

Reference News

DO-214AC/SMA	Schematic Diagram
	

Marking

SS32-MS	SS33-MS	SS34-MS	SS35-MS	SS36-MS
				
SS38-MS	SS310-MS	SS3150-MS	SS3200-MS	
				

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	SS32 -MS	SS33 -MS	SS34 -MS	SS35 -MS	SS36 -MS	SS38 -MS	SS310 -MS	SS3150 -MS	SS3200 -MS	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	150	200	V
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	105	140	V
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	150	200	V
Maximum average forward rectified current at TL(see fig.1)	I <sub(av)< sub=""></sub(av)<>	3.0									A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	80									A
Maximum instantaneous forward voltage at 3.0A	V _F	0.55			0.70		0.85			0.95	V
Maximum DC reverse current T _A =25℃ at rated DC blocking voltage T _A =125℃	I _R	0.5					0.3				mA
		5					3.0				
Typical junction capacitance (NOTE 1)	C _J	250			180						pF
Typical thermal resistance (NOTE 2)	R _{θJA}	70									℃/W
Operating junction temperature range	T _J	-55 to +125									℃
Storage temperature range	T _{STG}	-55 to +150									℃

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

Typical Characteristics

Fig.1 Forward Current Derating Curve

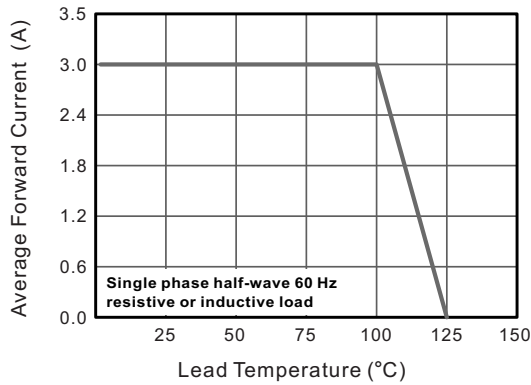


Fig.2 Typical Reverse Characteristics

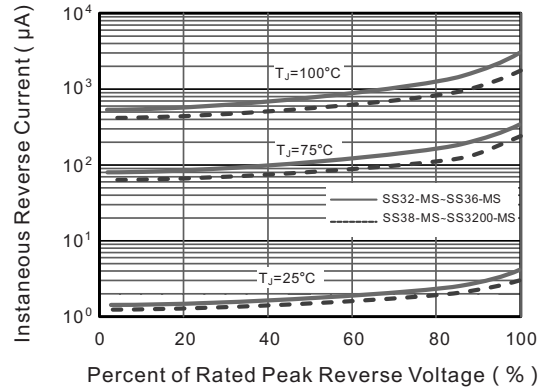


Fig.3 Typical Forward Characteristic

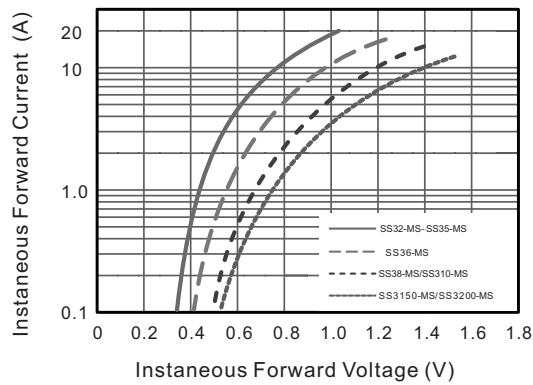


Fig.4 Typical Junction Capacitance

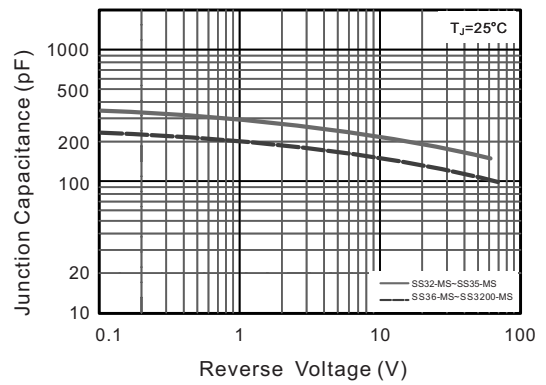


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

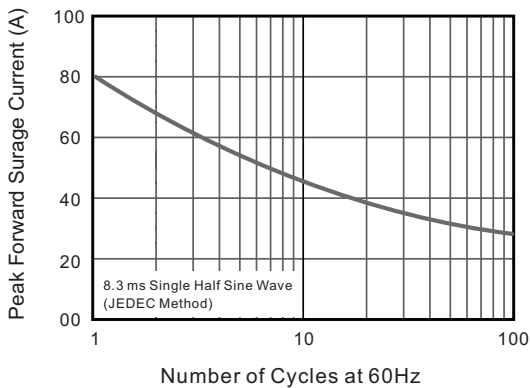
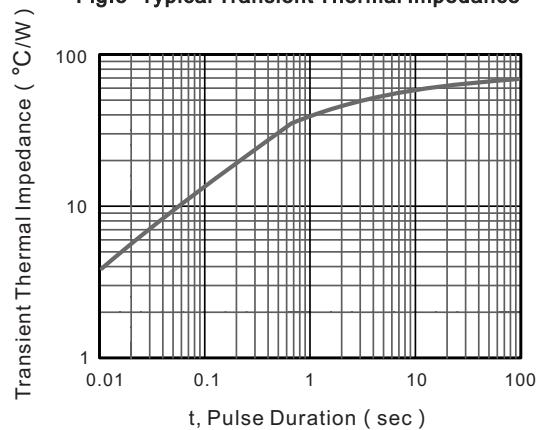
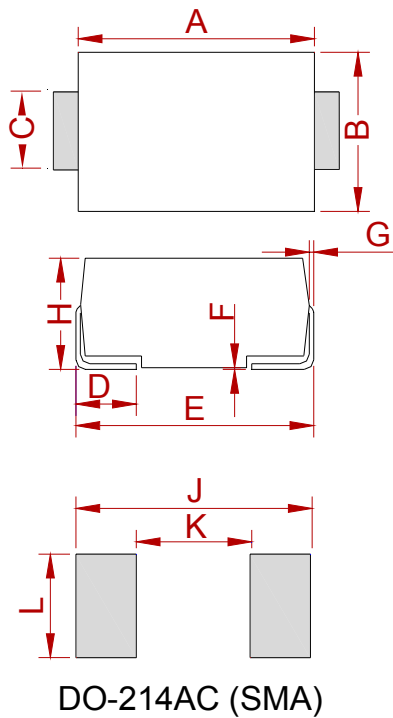


Fig.5- Typical Transient Thermal Impedance



PACKAGE MECHANICAL DATA



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.25	4.65	0.167	0.183
B	2.50	2.90	0.098	0.114
C	1.35	1.65	0.053	0.065
D	0.76	1.52	0.030	0.060
E	4.93	5.28	0.194	0.208
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	1.98	2.41	0.078	0.095
J	6.50		0.256	
K		2.30		0.090
L	1.70		0.067	

REEL SPECIFICATION

P/N	PKG	QTY
SS32-MS THRU SS3200-MS	SMA(DO-214AC)	2000

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